NEC

PNP SILICON TRANSISTORS 2SA1376,2SA1376A

DESCRIPTION

The 2SA1376/2SA1376A is designed for general-purpose applications requiring high Breakdown Voltages.

FEATURES

- High Breakdown Voltage.
 - $V_{CEO} = -180 \text{ V/}-200 \text{ V (2SA1376/2SA1376A)}$
- Good h_{FE} linearity.
- A Complementary pair with 2SC3478/2SC3478A.

ABSOLUTE MAXIMUM RATINGS

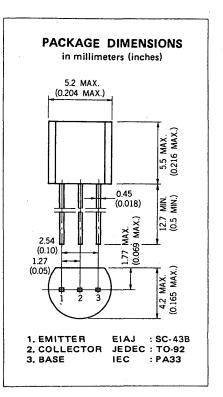
Maximum Temperatures

Maximum Voltages and Currents (Ta = 25 °C)

2SA1376/2SA1376A

-200V_{CBO} Collector to Base Voltage . . V_{CEO} Collector to Emitter Voltage VEBO Emitter to Base Voltage . . . -5.0٧ Collector Current (DC).... -100mΑ Collector Current (pulse)*... -200 mΑ Base Current (DC) -20mA

*PW ≤ 10 ms, Duty Cycle ≤ 50 %



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

2SA1376/2SA1376A

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE	DC Current Gain	135		400/600		V _{CE} = -10 V, I _C = -10 mA
ton	Turn-on Time		0.16		μς	I _C = -10 mA
toff	Turn-off Time		1.5		μs	$I_{B1} = -I_{B2} = -1 \text{ mA}, V_{CC} = -10 \text{ V}$
fŢ	Gain Bandwidth Product	80	120		MHz	$V_{CE} = -10 \text{ V, I}_{E} = 10 \text{ mA}$
C _{ob}	Output Capacitance		3.5	4.0	рF	$V_{CB} = -30 \text{ V, I}_F = 0, f = 1.0 \text{ MHz}$
СВО	Collector Cutoff Current			-100	nΑ	$V_{CB} = -200 \text{ V, I}_{E} = 0$
I _{EBO}	Emitter Cutoff Current			-100	nΑ	$V_{EB} = -4.0 \text{ V, I}_{C} = 0$
V BE	Base to Emitter Voltage	-600	-650	-700	mV	$V_{CE} = -10 \text{ V, I}_{C} = -10 \text{ mA}$
V _{CE(sat)}	Collector Saturation Voltage		-0.2	-0.3	V	$I_C = -50 \text{ mA}, I_B = -5.0 \text{ mA}$
V _{BE(sat)}	Base Saturation Voltage		-0.8	-1.2	V	$I_C = -50 \text{ mA}, I_B = -5.0 \text{ mA}$

Classification of hFE

Rank	L	κ	U**
Range	135 – 270	200 – 400	300 – 600

Test Conditions: $V_{CE} = -10 \text{ V}$, $I_{C} = -10 \text{ mA}$

^{** 2}SA1376A has no U rank.

TYPICAL CHARACTERISTICS (Ta = 25 °C)

